

Features

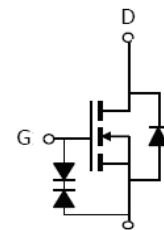
- Enhancement mode
- Low on-resistance $R_{DS(on)}$ @ $V_{GS}=10V$
- Super Junction Technology
- ESD Protection HBM 8KV
- Pb-free lead plating; RoHS compliant; Halogen free


Halogen-Free

Part ID	Package Type	Marking	Tube Information
VSF190N70HS2	TO-220WF	190N70H	50pcs/Tube

V_{DS}	700	V
$R_{DS(on),TYP@ V_{GS}=10V}$	150	m Ω
I_D	20	A

TO-220WF



Maximum ratings, at $T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit	
$V_{(BR)DSS}$	Drain-Source breakdown voltage	700	V	
V_{GS}	Gate-Source voltage	± 30	V	
I_S	Diode continuous forward current	$T_C = 25^\circ\text{C}$	20	A
I_D	Continuous drain current @ $V_{GS}=10V$	$T_C = 25^\circ\text{C}$	20	A
		$T_C = 100^\circ\text{C}$	13	A
I_{DM}	Pulse drain current tested ①	$T_C = 25^\circ\text{C}$	80	A
EAS	Avalanche energy, single pulsed ②	640	mJ	
P_D	Maximum power dissipation	$T_C = 25^\circ\text{C}$	30	W
		$T_C = 100^\circ\text{C}$	12	W
T_{STG}, T_J	Storage and Junction Temperature Range	-55 to 150	$^\circ\text{C}$	

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	4.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_j = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	700	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =700V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _j =125°C)	V _{DS} =560V, V _{GS} =0V	--	--	50	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±30V, V _{DS} =0V	--	--	±5	μA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	3.0	--	4.3	V
R _{DS(ON)}	Drain-Source On-State Resistance ③	V _{GS} =10V, I _D =10A	--	150	190	mΩ
		T _j =100°C	--	230	--	mΩ
Dynamic Electrical Characteristics @ T_j= 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	1570	1850	2130	pF
C _{oss}	Output Capacitance		725	855	985	pF
C _{riss}	Reverse Transfer Capacitance		25	35	45	pF
Q _g	Total Gate Charge	V _{DS} =350V, I _D =10A, V _{GS} =10V	--	39	--	nC
Q _{gs}	Gate-Source Charge		--	11	--	nC
Q _{gd}	Gate-Drain Charge		--	14	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =350V, I _D =10A, R _G =10Ω, V _{GS} =10V	--	39	--	ns
t _r	Turn-on Rise Time		--	32	--	ns
t _{d(off)}	Turn-Off Delay Time		--	121	--	ns
t _f	Turn-Off Fall Time		--	29	--	ns
Source- Drain Diode Characteristics@ T_j= 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =10A, V _{GS} =0V	--	0.9	1.2	V
t _{rr}	Reverse Recovery Time	T _j =25°C, I _{sd} =10A, V _{GS} =0V	--	280	--	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	--	3.7	--	μC

NOTE: ① Repetitive rating; pulse width limited by max junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 26mH, R_G = 25Ω, I_{AS} = 7A, V_{GS} = 10V. Part not recommended for use above this value.

③ Pulse width ≤ 380μs; duty cycle ≤ 2%.

Typical Characteristics

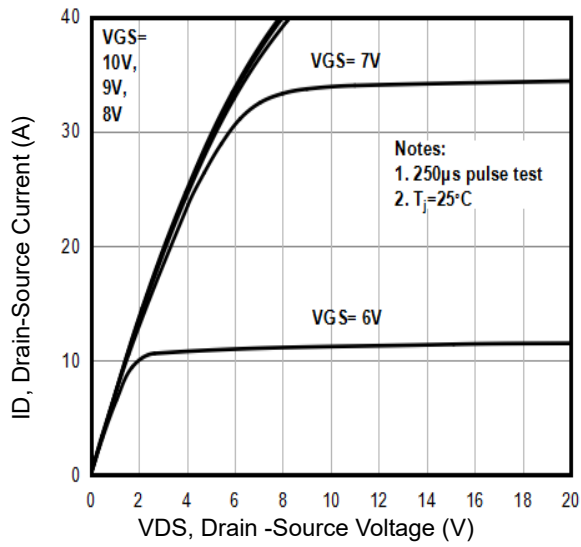


Fig1. Typical Output Characteristics

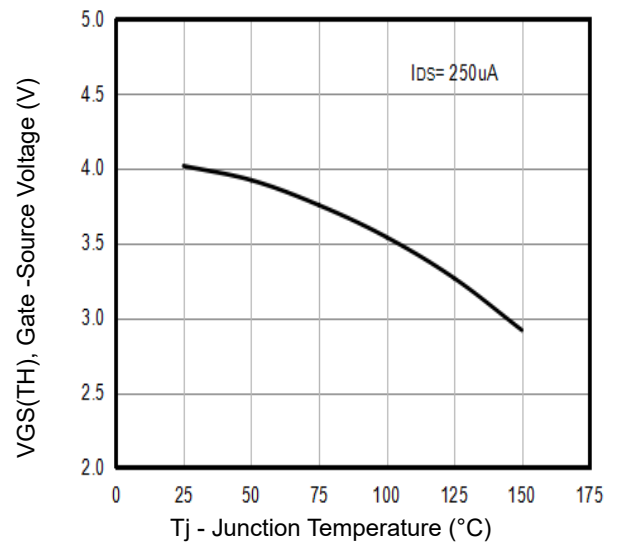


Fig2. $V_{GS(TH)}$ Gate -Source Voltage Vs. T_j

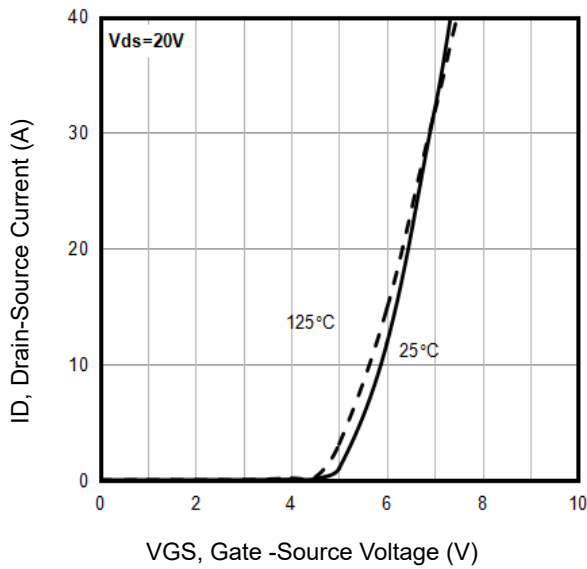


Fig3. Typical Transfer Characteristics

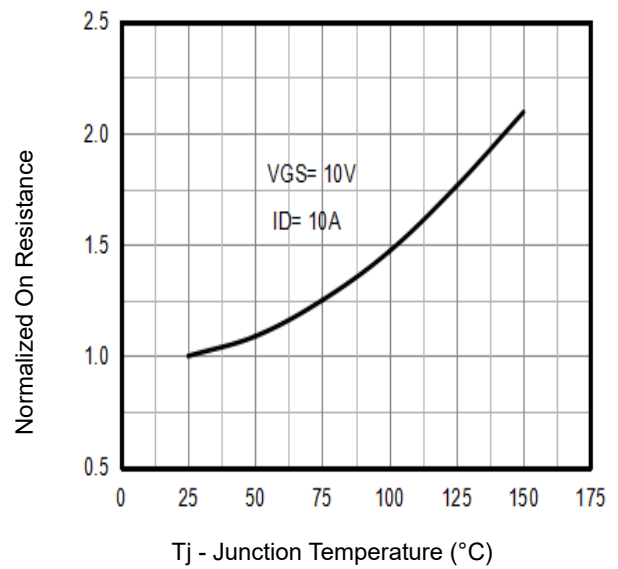


Fig4. Normalized On-Resistance Vs. Temperature

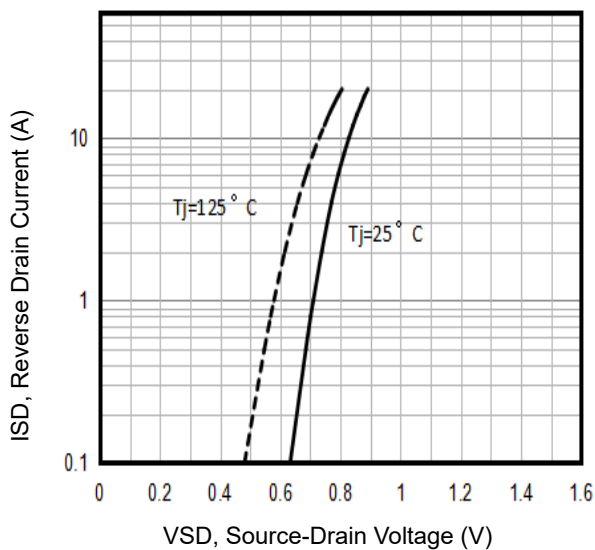


Fig5. Typical Source-Drain Diode Forward Voltage

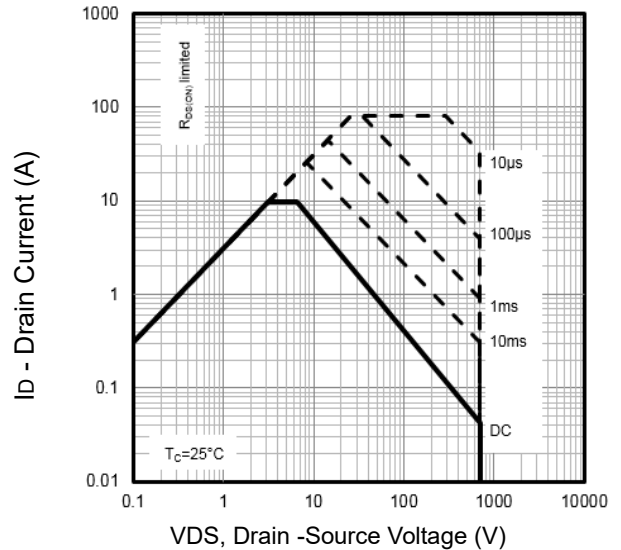


Fig6. Maximum Safe Operating Area

Typical Characteristics

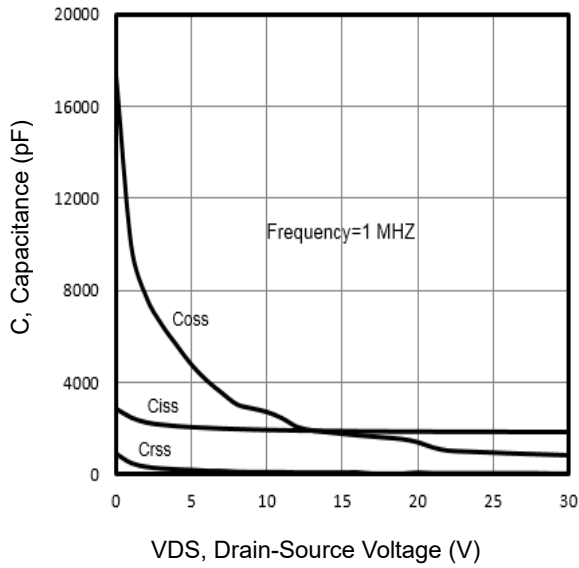


Fig7. Typical Capacitance Vs. Drain-Source Voltage

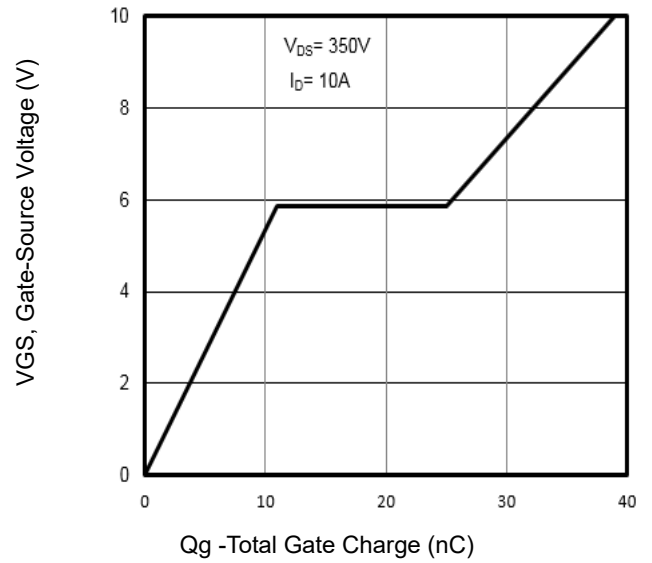


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

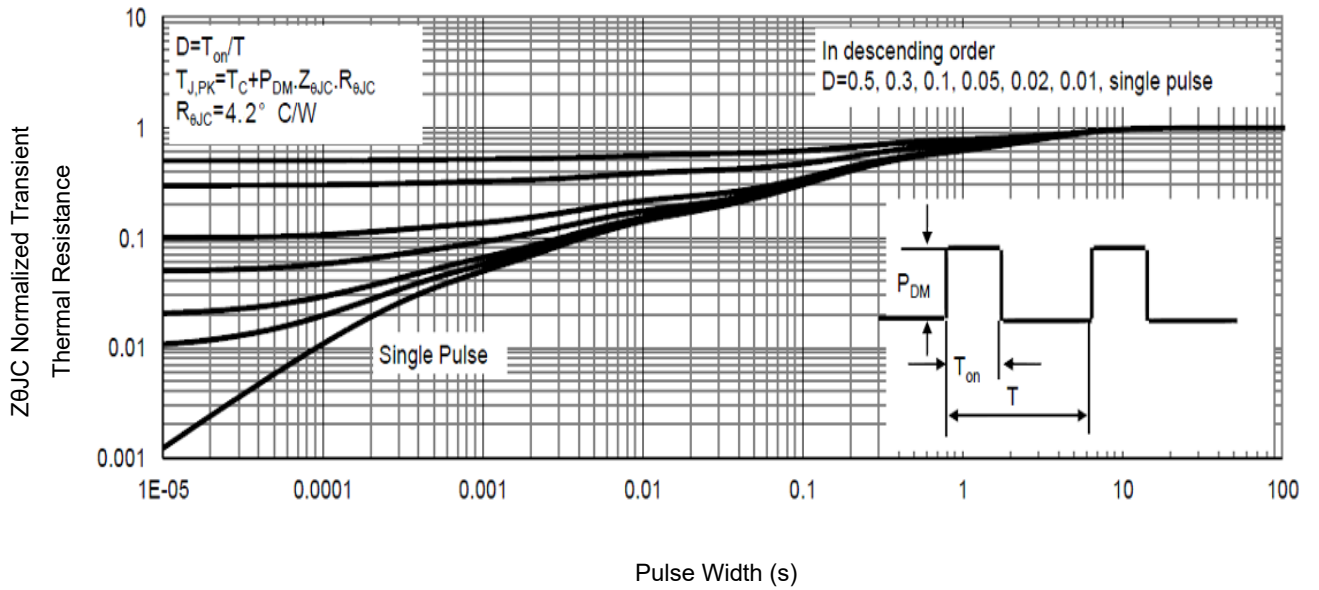


Fig9. Normalized Maximum Transient Thermal Impedance

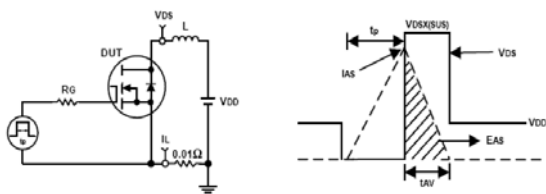


Fig10. Unclamped Inductive Test Circuit and waveforms

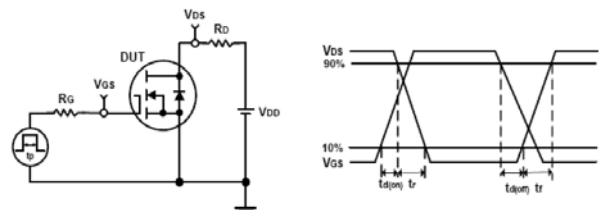
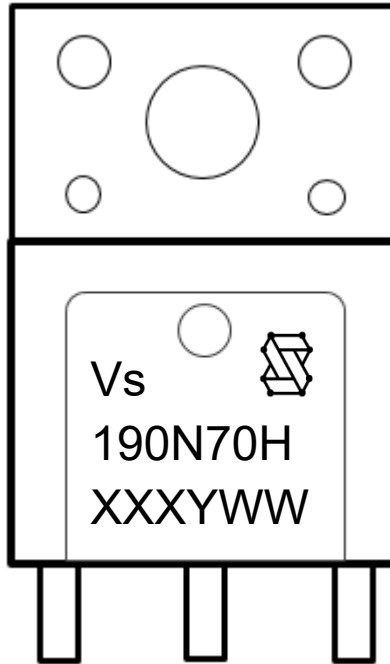


Fig11. Switching Time Test Circuit and waveforms

Marking Information



1st line: Vanguard Code (Vs), Vanguard Logo

2nd line: Part Number (190N70H)

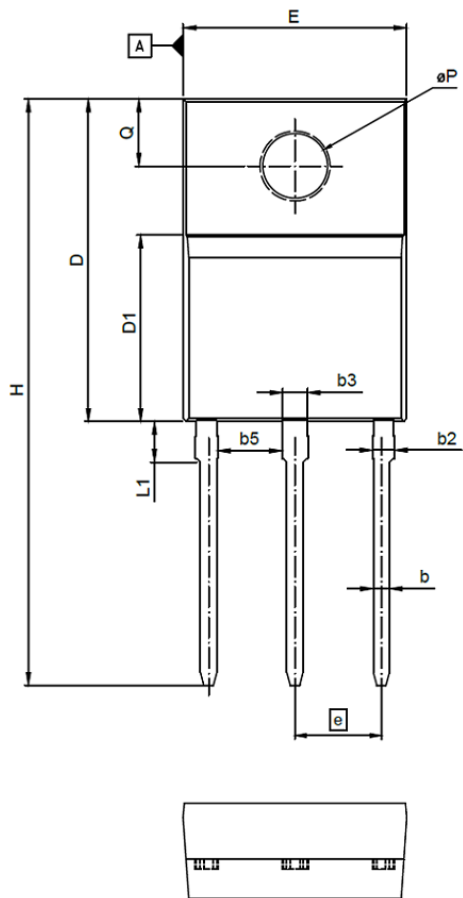
3rd line: Date code (XXXYYWW)

XXX: Wafer Lot Number Code, code changed with Lot Number

Y: Year Code, (e.g. E=2017, F=2018, G=2019, H=2020, etc)

WW: Week Code (01 to 53)

TO-220WF Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	2.65	2.76	2.95
b	0.75	0.80	0.90
b2	0.98	1.08	1.26
b3	1.00	1.20	1.40
b5	3.00	--	--
c	0.40	0.50	0.60
D	15.47	15.87	16.27
D1	--	9.17	--
E	10.70	11.00	11.30
e	3.95	4.25	4.55
H	28.25	28.85	29.45
L	12.58	12.98	13.38
L1	1.70	2.00	2.30
øP	2.98	3.18	3.38
Q	3.10	3.30	3.50

Note:

1. Dimensions do NOT include mold flash, protrusions or gate burrs.

Customer Service

Sales and Service:

sales@vgsemi.com

Vanguard Semiconductor CO., LTD

TEL: (86-755) -26902410

FAX: (86-755) -26907027

WEB: www.vgsemi.com